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MCH6123

Bipolar Transistor -50V, -3A, Low VCE(sat), PNP Single MCPH6

Applications

- DC-DC converter, relay drivers, lamp drivers, motor drivers

Features

- Adoption of MBIT process
- Low collector-to-emitter saturation voltage
- Ultrasmall-sized package permitting applied sets to be made small and slim (0.85mm)
- High allowable power dissipation
- Large current capacity
- High speed switching

Specifications

Absolute Maximum Ratings at Ta=25°C

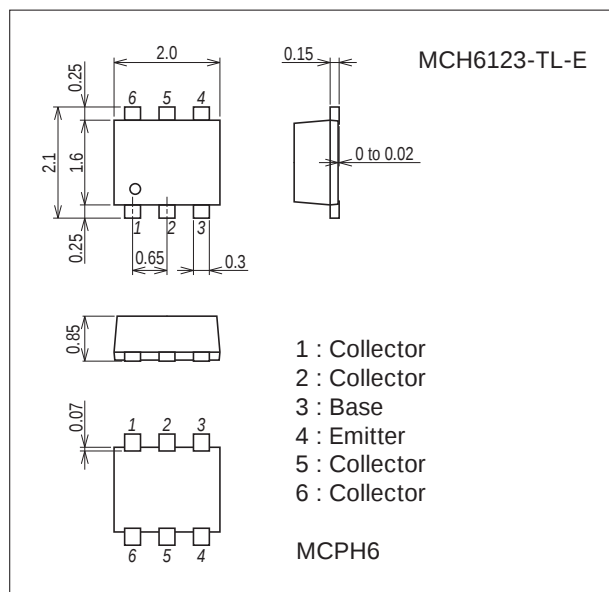
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-50	V
Collector-to-Emitter Voltage	VCEs		-50	V
Collector-to-Emitter Voltage	VCEO		-50	V
Emitter-to-Base Voltage	VEBO		-6	V
Collector Current	IC		-3	A
Collector Current (Pulse)	ICP		-6	A
Base Current	IB		-600	mA
Collector Dissipation	PC	When mounted on ceramic substrate (600mm ² ×0.8mm)	1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

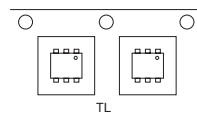
7022A-007



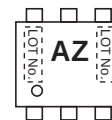
Product & Package Information

- Package : MCPH6
- JEITA, JEDEC : SC-88, SC-70-6, SOT-363
- Minimum Packing Quantity : 3,000 pcs./reel

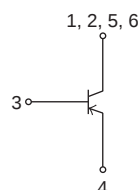
Packing Type : TL



Marking



Electrical Connection

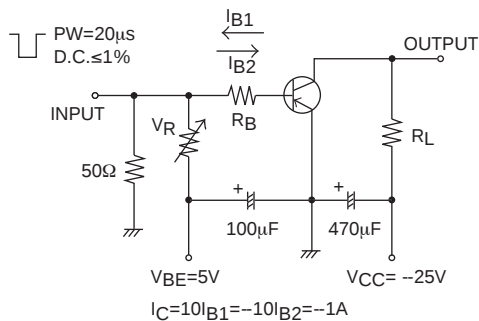


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Electrical Characteristics at Ta=25°C

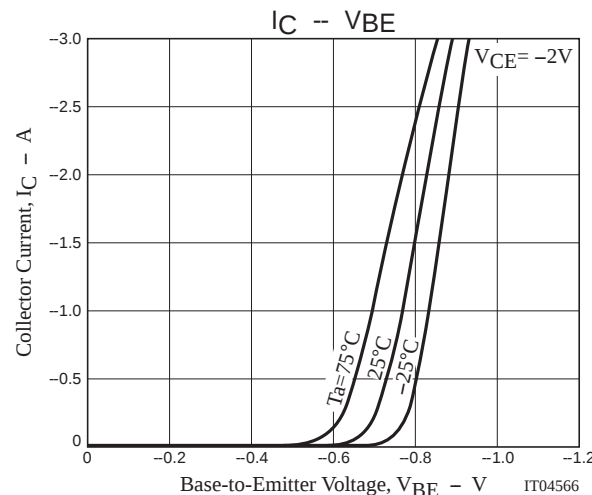
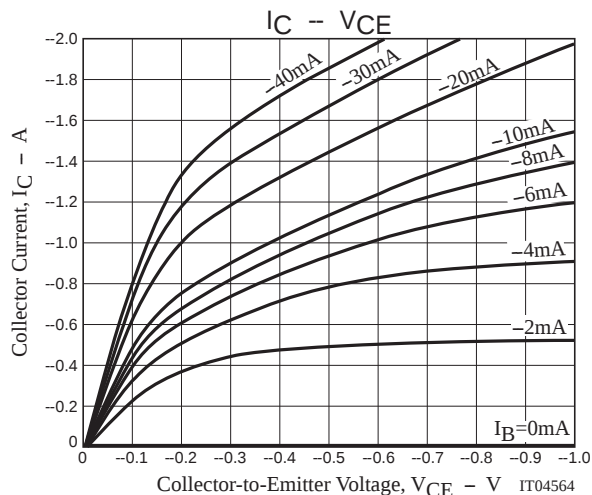
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	VCE= -40V, IE=0A			-1	μA
Emitter Cutoff Current	IEBO	VEB= -4V, IC=0A			-1	μA
DC Current Gain	hFE	VCE= -2V, IC= -100mA	200		560	
Gain-Bandwidth Product	fT	VCE= -10V, IC= -500mA		390		MHz
Output Capacitance	Cob	VCE= -10V, f=1MHz		24		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)1	IC= -1A, IB= -50mA		-115	-230	mV
	VCE(sat)2	IC= -2A, IB= -100mA		-240	-650	mV
Base-to-Emitter Saturation Voltage	VBE(sat)	IC= -2A, IB= -100mA		-0.88	-1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC= -10μA, IE=0A	-50			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	IC= -100μA, RE=0Ω	-50			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC= -1mA, RE=∞	-50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE= -10μA, IC=0A	-6			V
Turn-On Time	ton	See specified Test Circuit.		30		ns
Storage Time	tstg			230		ns
Fall Time	tf			18		ns

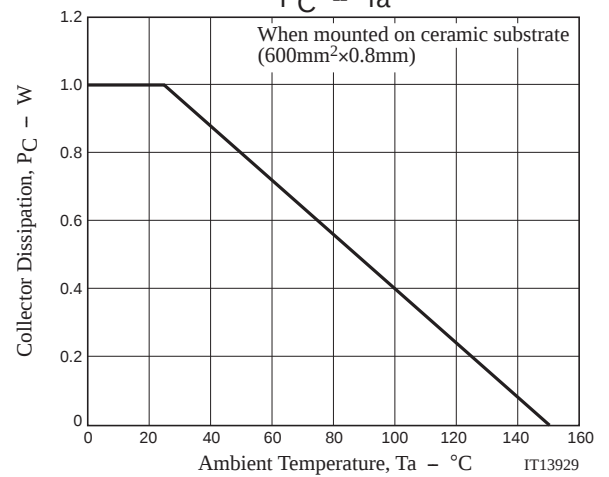
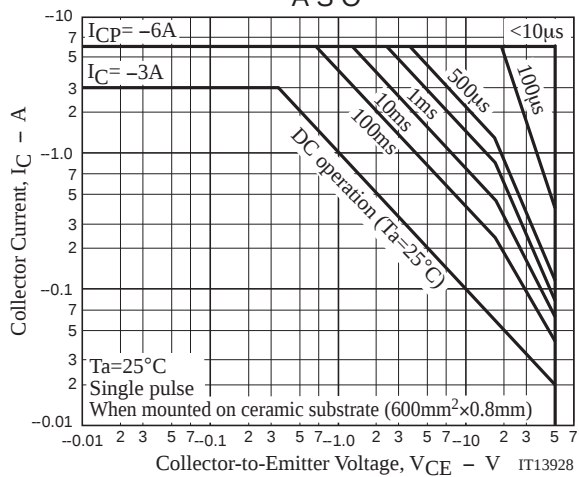
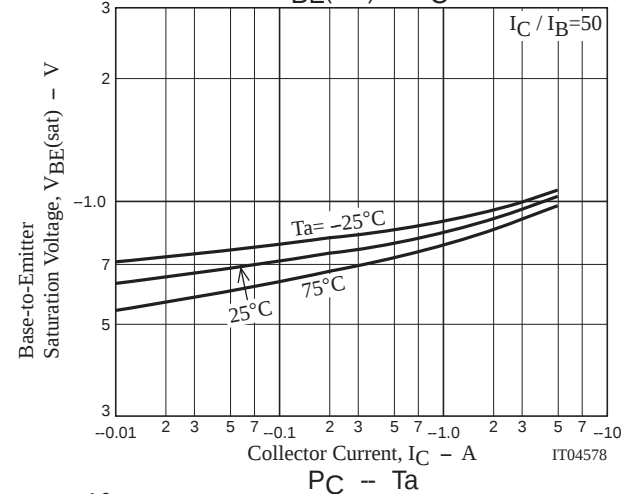
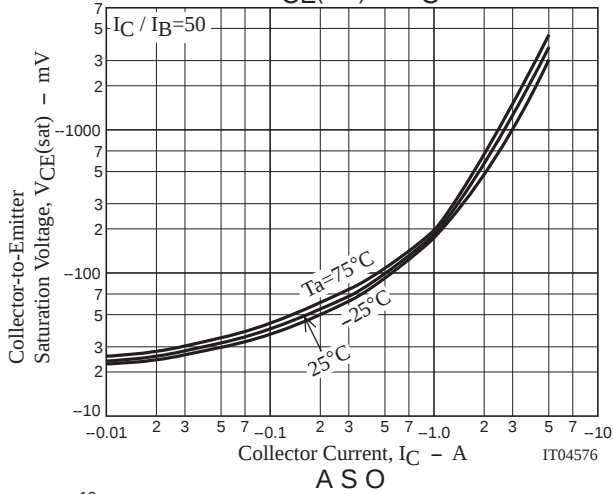
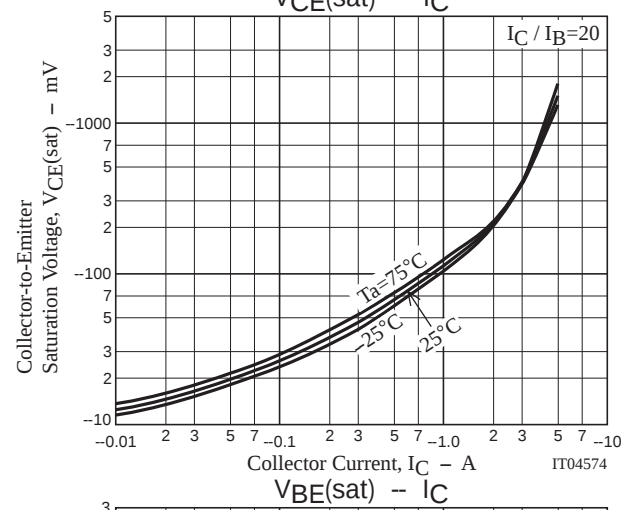
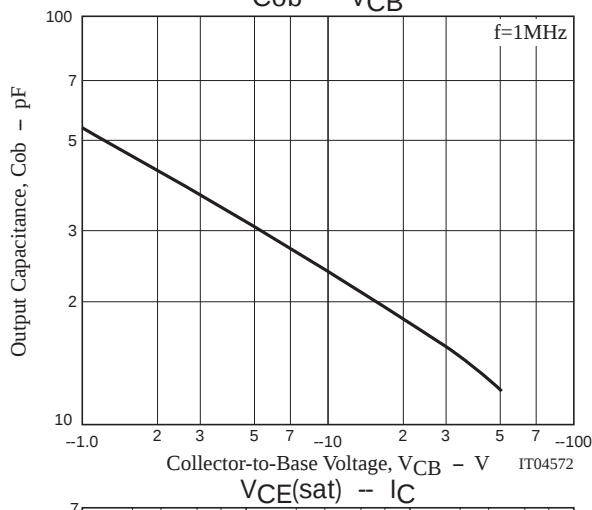
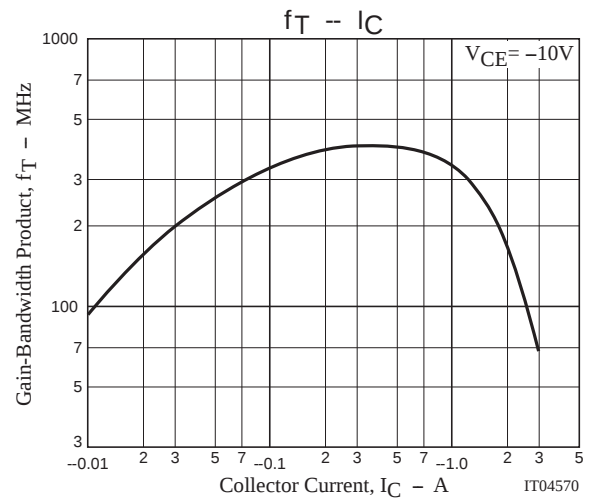
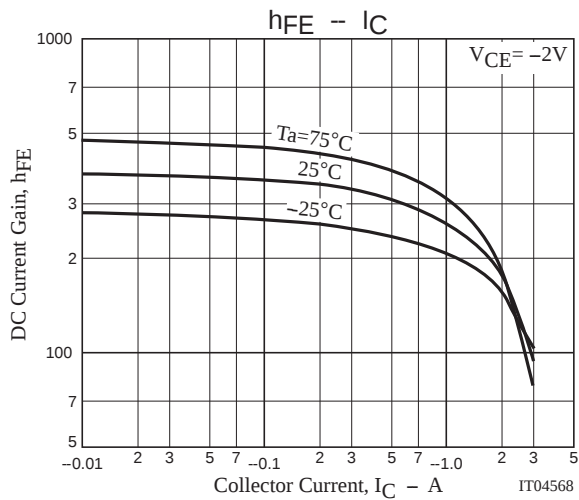
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
MCH6123-TL-E	MCPH6	3,000pcs./reel	Pb Free





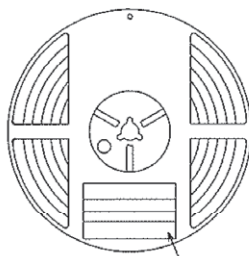
Embossed Taping Specification

MCH6123-TL-E

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
MCPH6	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

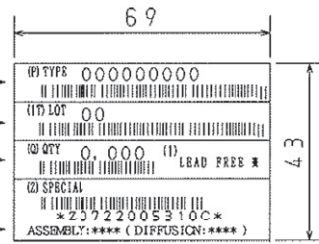
Packing method



Reel label

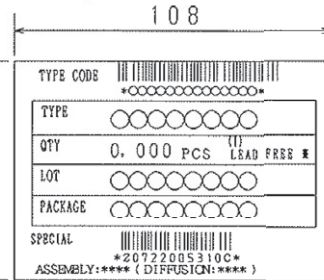
Type No.
LOT No.
Quantity
Origin

Reel label, Inner box label
(unit:mm)



Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical
distribution process.



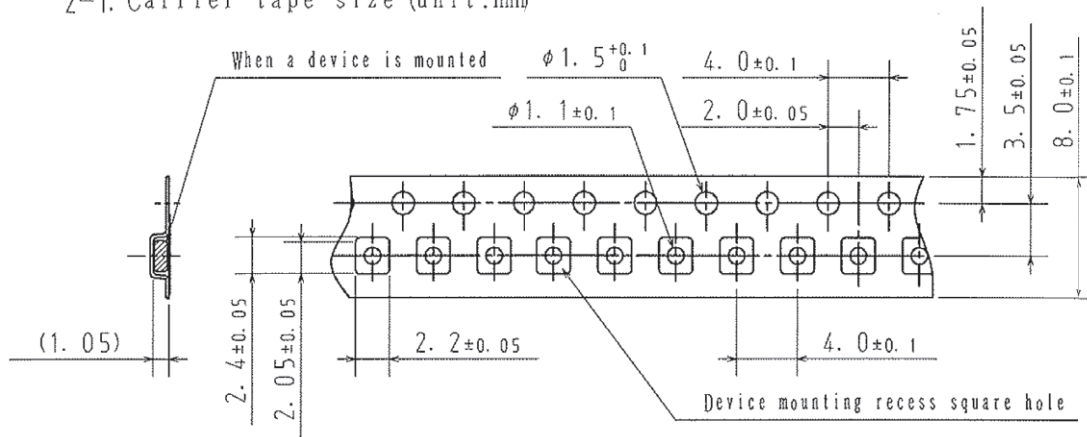
NOTE (1)

The LEAD FREE * description shows that the surface
treatment of the terminal is lead free.

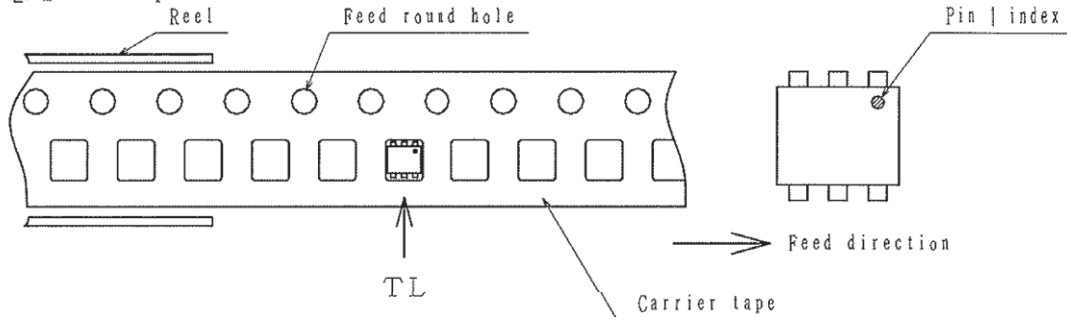
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



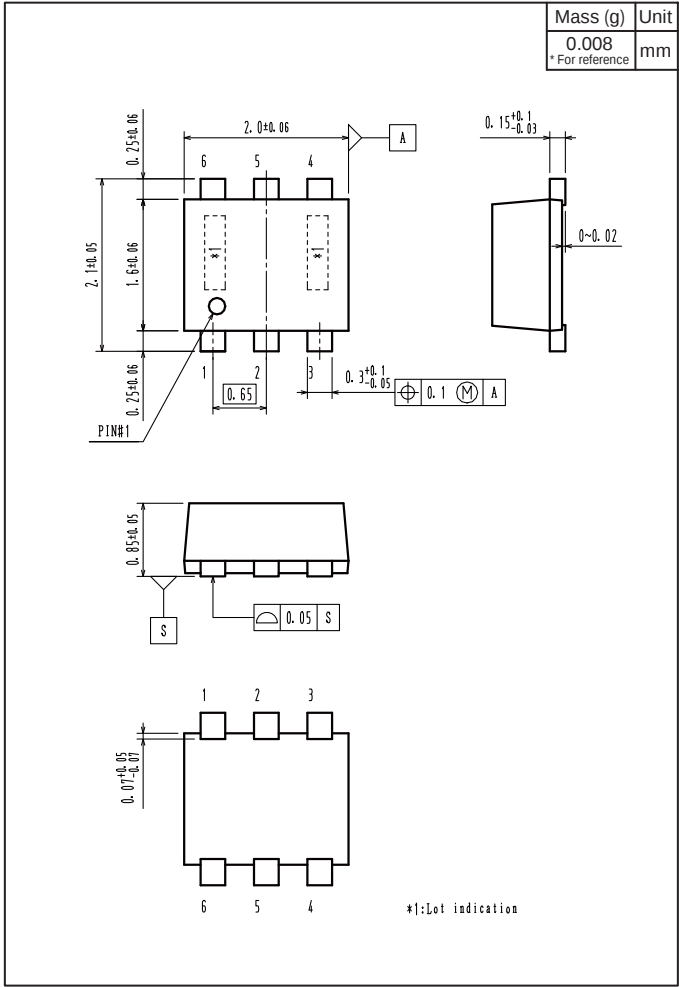
2-2. Device placement direction



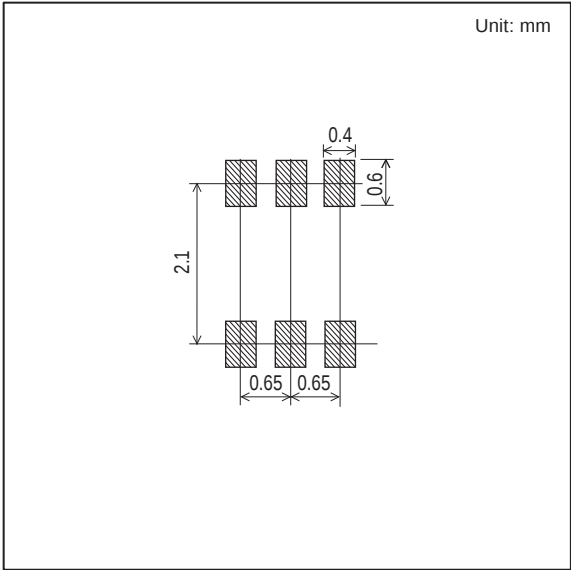
Those with pin 1 index on the feed hole side.....TL

MCH6123

Outline Drawing
MCH6123-TL-E



Land Pattern Example



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